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First Named Inventor	Leonard Forbes
Serial No.	10/785,310
Filing Date	February 24, 2004
Group Art Unit	2818
Examiner Name	Unknown
Confirmation No.	9673
Attorney Docket No.	400.264US01

**GENERAL  
TRANSMITTAL  
FORM UNDER 37 CFR 1.8  
(LARGE ENTITY)**

Title: 4F2 EEPROM NROM MEMORY ARRAYS WITH VERTICAL DEVICES

Mail Stop Amendment  
Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

**Enclosures**

The following documents are enclosed:

Information Disclosure Statement (1 pg.); Form 1449 (7 pgs.); 61 copies of cited references; U.S. reference(s) not included pursuant to 37 C.F.R. 1.98 (c)(2)(i);  
 An itemized return-receipt postcard

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**CUSTOMER NO. 27073**

**Submitted By**

Name	Andrew C. Walseth	Reg. No.	43,234	Telephone	(612) 312-2207
Signature				Date	6/1/04

**Certificate of Mailing**

I certify that this correspondence and the identified documents listed on this transmittal are being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450 on June 1, 2004.

Name	Rhonda L. Foley	Signature	
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(LARGE ENTITY TRANSMITTAL UNDER 37 CFR § 1.8)



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## INFORMATION DISCLOSURE STATEMENT

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In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

As an Office Action has not yet issued in this application, Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373. If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2207.

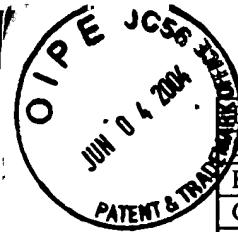
Respectfully submitted,

Date: 6/1/04

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FORM PTO-1449**

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